

EVVOSEMI[®]

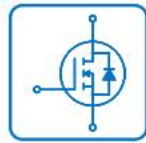
THINK CHANGE DO



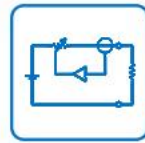
ESD



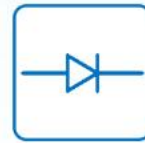
TVS



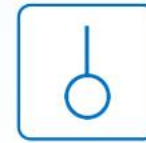
MOS



LDO



Diode



Sensor



DC-DC

Product Specification

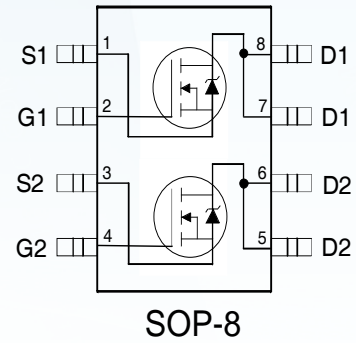
▶ Domestic	Part Number	IRF7303
▶ Overseas	Part Number	IRF7303
▶ Equivalent	Part Number	IRF7303

EV is the abbreviation of name EVVO

Dual N-Channel MOSFET

Features

- $V_{DS} (V) = 30V$
- $I_D = 5.3 A$
- $R_{DS(ON)} < 50m\Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 80m\Omega$ ($V_{GS} = -4.5V$)
- Generation VTechnology
- Ultra Low On-Resistance
- Surface Mount
- Dynamic dv/dt Rating
- Fast Switching
- Lead-Free



Description

The SOP-8 has been modied through a customizcec leadframe for enhanced thermal characteristics and multiple die capability making it ideal in a variety of power applications.

With these improvements, multiple devices can be used in an application with dramatically reduced board space.

The package is designed for vapor phase, intra red, or wave soldering techniques. Power dissipation of gre-ater than 0.8W is possible in a typical PCB mount app-lication.

Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ C$	10 Sec. Pulsed Drain Current, $V_{GS} @ 10V$	5.3	A
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	4.9	
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	3.9	
I_{DM}	Pulsed Drain Current $\text{\textcircled{D}}$	20	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.0	W
	Linear Derating Factor	0.016	W/ $^\circ C$
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt $\text{\textcircled{D}}$	5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

Thermal Resistance Ratings

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient $\text{\textcircled{D}}$		62.5	$^\circ C/W$

Dual N-Channel MOSFET

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

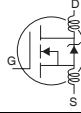
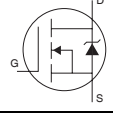
	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	30			V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient		0.032		V/°C	Reference to 25°C, I _D = 1mA
R _{DS(ON)}	Static Drain-to-Source On-Resistance			50 80	mΩ	V _{GS} = 10V, I _D = 2.4A ③ V _{GS} = 4.5V, I _D = 2.0A ③
V _{GS(th)}	Gate Threshold Voltage	1.0			V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	5.2			S	V _{DS} = 15V, I _D = 2.4A
I _{DSS}	Drain-to-Source Leakage Current			1.0 25	μA	V _{DS} = 24V, V _{GS} = 0V V _{DS} = 24V, V _{GS} = 0V, T _J = 125 °C
I _{GSS}	Gate-to-Source Forward Leakage Gate-to-Source Reverse Leakage			100 -100	nA	V _{GS} = 20V V _{GS} = - 20V
Q _g	Total Gate Charge			25	nC	I _D = 2.4A
Q _{gs}	Gate-to-Source Charge			2.9	nC	V _{DS} = 24V
Q _{gd}	Gate-to-Drain ("Miller") Charge			7.9	nC	V _{GS} = 10V, See Fig. 6 and 12 ③
t _{d(on)}	Turn-On Delay Time		6.8		ns	V _{DD} = 15V I _D = 2.4A R _G = 6.0Ω R _D = 6.2Ω, See Fig. 10 ③
t _r	Rise Time		21			
t _{d(off)}	Turn-Off Delay Time		22			
t _f	Fall Time		7.7			
L _D	Internal Drain Inductance		4.0		nH	Between lead tip and center of die contact 
L _S	Internal Source Inductance		6.0			
C _{iss}	Input Capacitance		520		pF	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz, See
C _{oss}	Output Capacitance		180			
C _{rss}	Reverse Transfer Capacitance		72			

Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)			2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①			20		
V _{SD}	Diode Forward Voltage			1.0	V	T _J = 25°C, I _S = 1.8A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time		47	71	ns	T _J = 25°C, I _F = 2.4A
Q _{rr}	Reverse Recovery Charge		56	84	nC	di/dt = 100A/μs ③
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② I_{SD} ≤ 2.4A, di/dt ≤ 73A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ④ Surface mounted on FR-4 board, t ≤ 10sec.

Dual N-Channel MOSFET

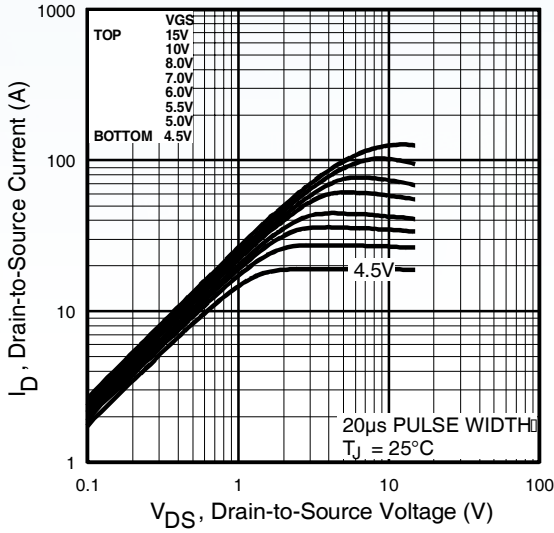


Fig 1. Typical Output Characteristics

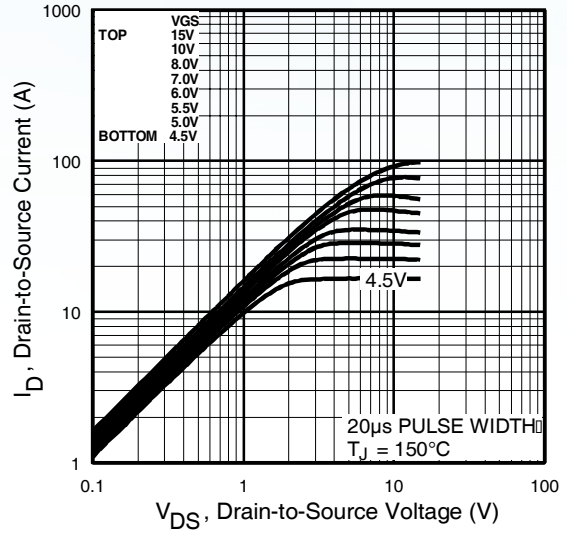


Fig 2. Typical Output Characteristics

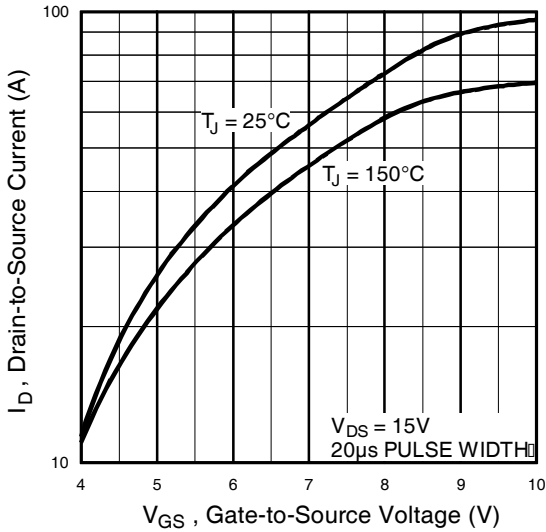


Fig 3. Typical Transfer Characteristics

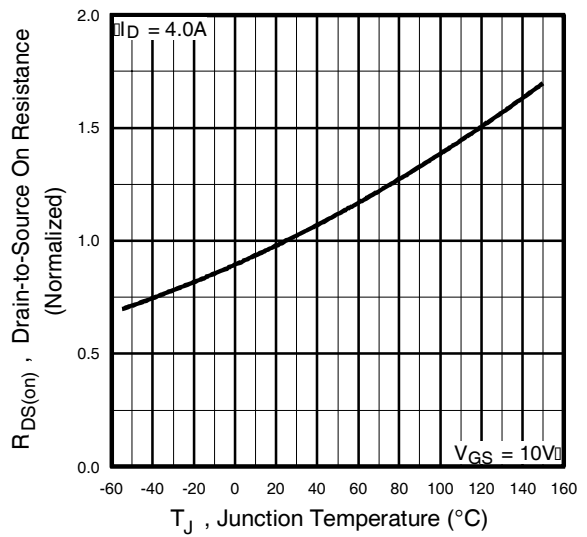


Fig 4. Normalized On-Resistance Vs. Temperature

Dual N-Channel MOSFET

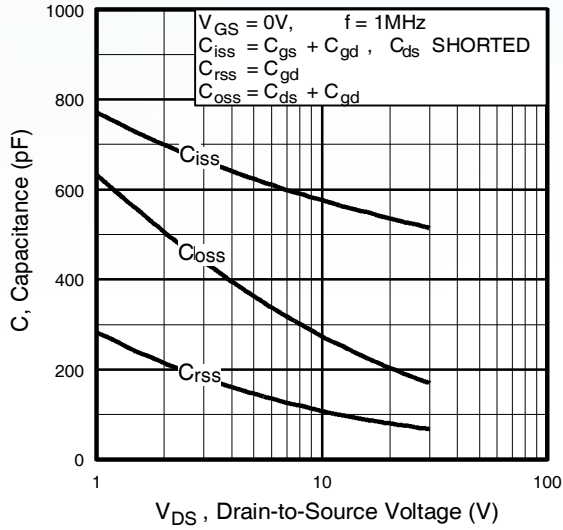


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

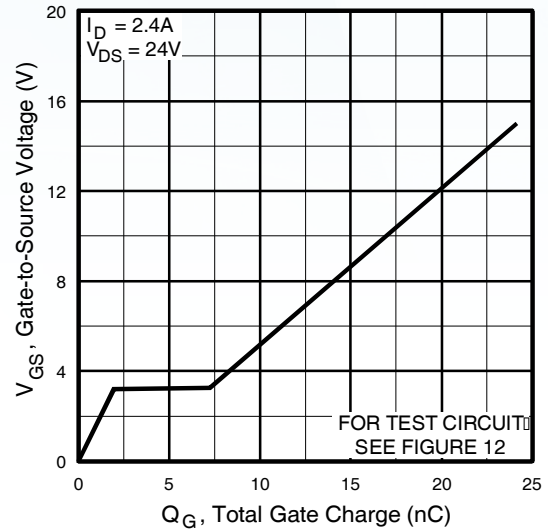


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

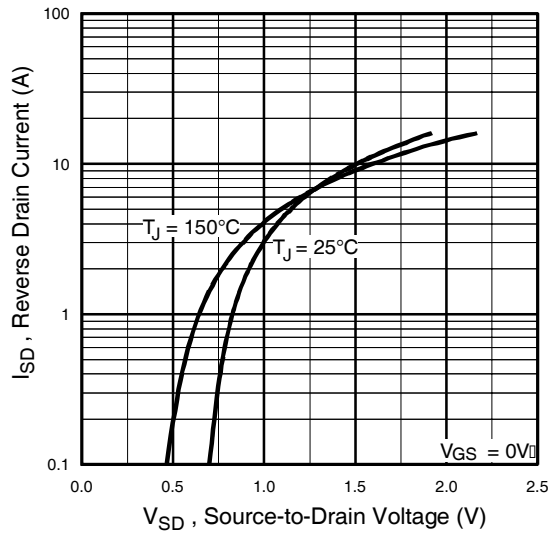


Fig 7. Typical Source-Drain Diode Forward Voltage

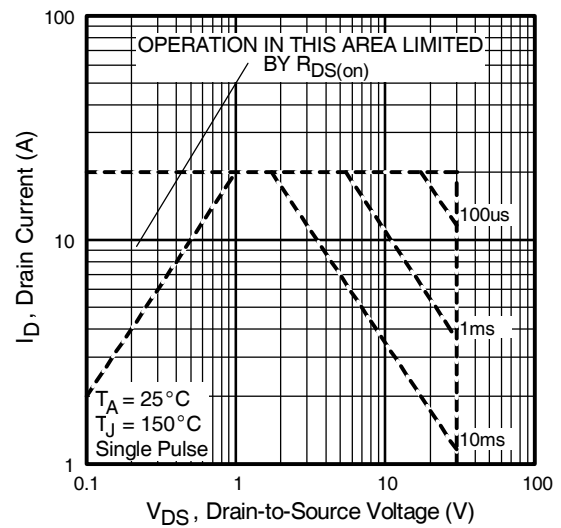


Fig 8. Maximum Safe Operating Area

Dual N-Channel MOSFET

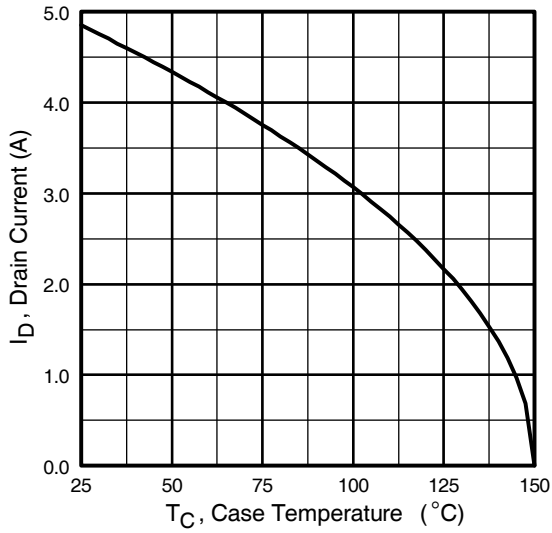


Fig 9. Maximum Drain Current Vs. Ambient Temperature

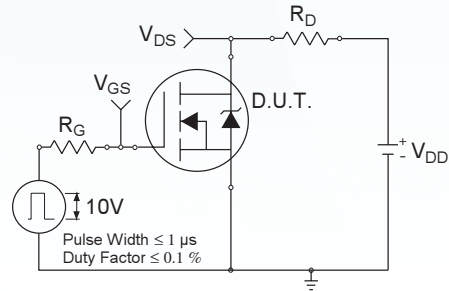


Fig 10a. Switching Time Test Circuit

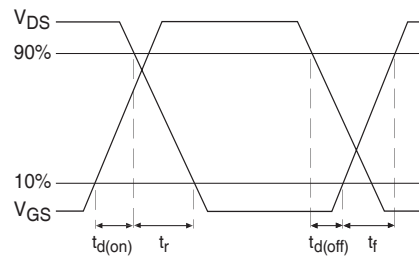


Fig 10b. Switching Time Waveforms

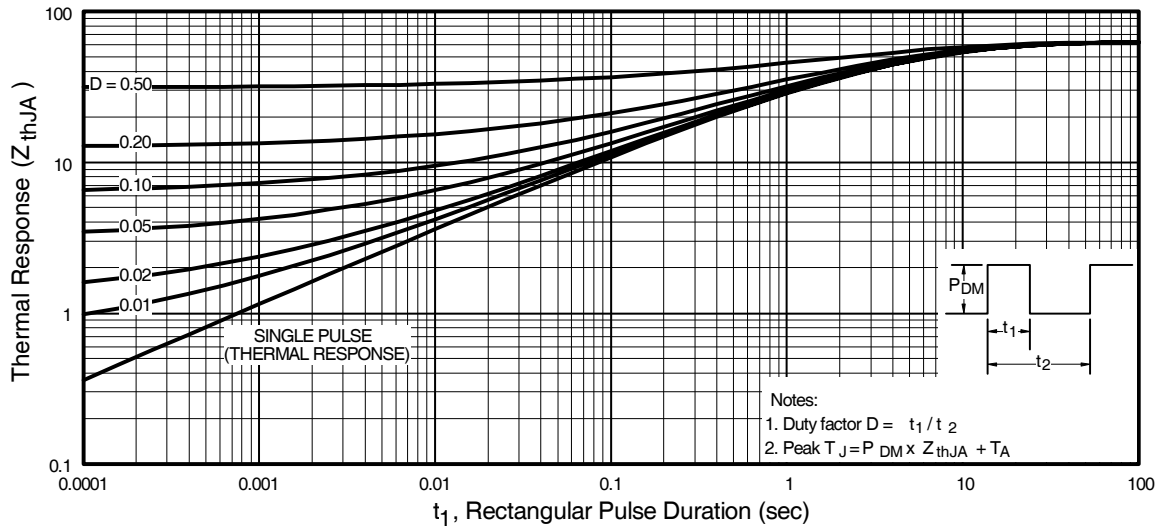


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Dual N-Channel MOSFET

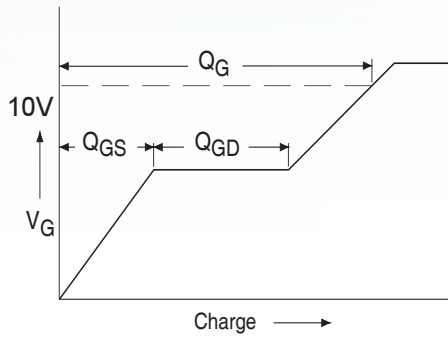


Fig 12a. Basic Gate Charge Waveform

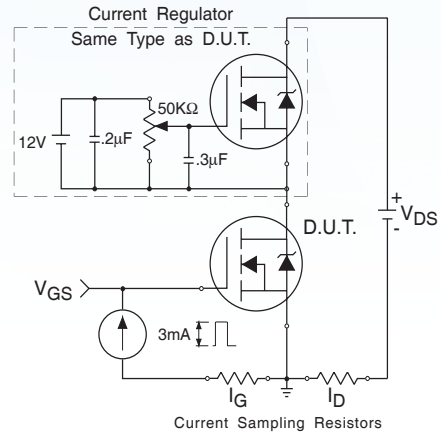
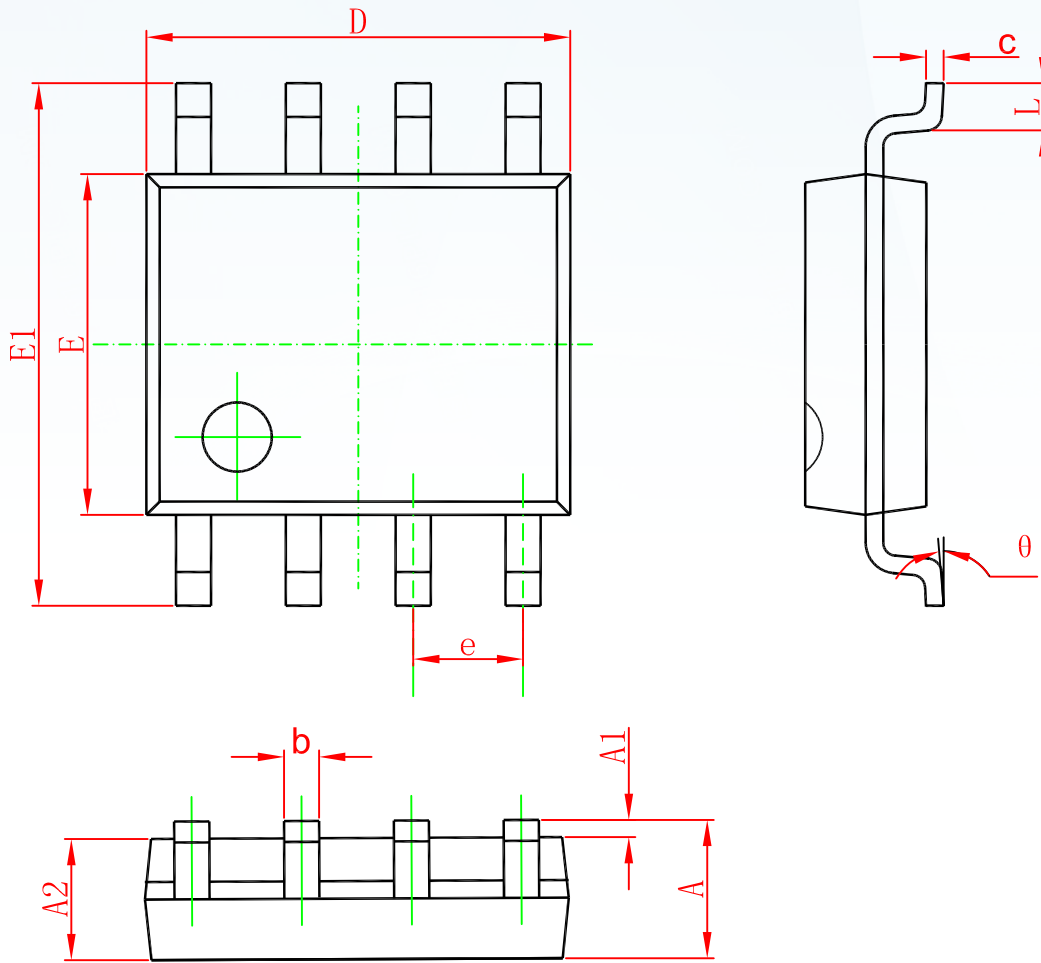


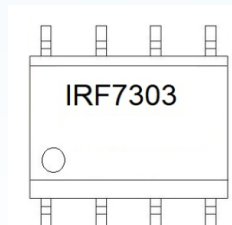
Fig 12b. Gate Charge Test Circuit

SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
IRF7303	SOP-8	3000	Tape and reel

Disclaimer

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